

Description

The BSR802N uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

D G SOT-23-3L

General Features

 $V_{DS} = 20V I_{D} = 6 A$

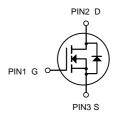
 $R_{DS(ON)}$ < 27m Ω @ V_{GS} =4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
BSR802N	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter		Limit	Unit	
V _{DS}	Drain-Source Voltage		20	V	
V _G S	Gate-Source Voltage		±12	V	
I _D	Continuous Drain Current	T _A =25℃	6	А	
		T _A =70℃	3.6		
Ірм	Drain Current-Pulsed (Note 1)		15	Α	
P _D	Maximum Power Dissipation		1.25	W	
Тյ,Тѕтс	Operating Junction and Storage Temperature Range		-55 To 150	$^{\circ}$ C	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)		100	°CM	

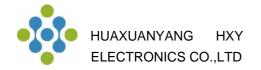


Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	22.5	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =20V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.65	1.0	V
	RDS(ON)	V _{GS} =4.5V, I _D =4.0 A	-	22	27	mΩ
Drain-Source On-State Resistance		V _{GS} =2.5V, I _D =4.5A	-	28	40	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =4A	-	10	-	S
Input Capacitance	Clss	V _{DS} =8V,V _{GS} =0V,	-	500	-	PF
Output Capacitance	Coss		-	295	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	96	-	PF
Turn-on Delay Time	t d(on)		-	11	-	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =1A	-	30	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =4.5V, R_{GEN} =6 Ω	-	35	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =3A,V _{GS} =4.5V	-	10	15	nC
Gate-Source Charge	Qgs		-	2.3	-	nC
Gate-Drain Charge	Q _{gd}		-	2.9	-	nC
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =1A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	4.5	Α

Notes:

- $\textbf{1.} \ \ \textbf{Repetitive rating: pulse width limited by maximum junction temperature.}$
- **2.** Surface mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

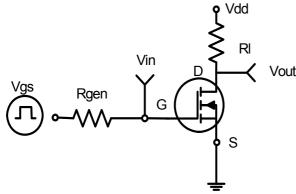


Figure 1:Switching Test Circuit

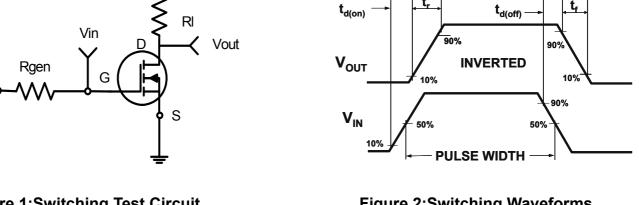
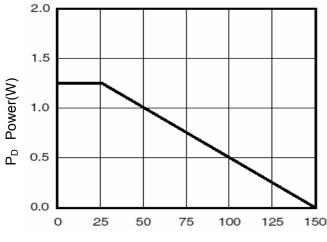
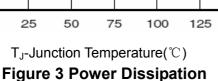


Figure 2:Switching Waveforms





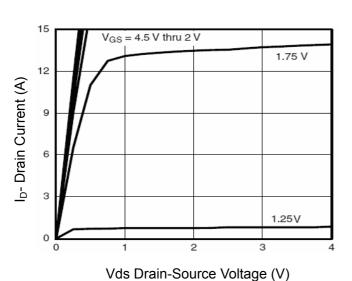
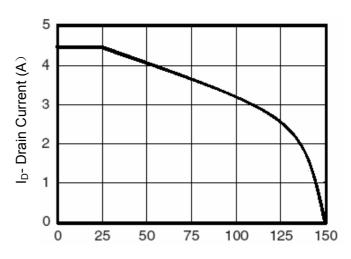
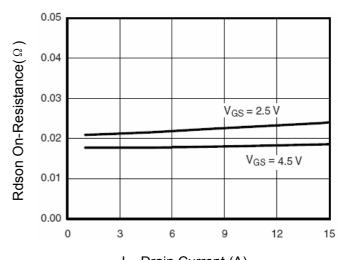


Figure 5 Output Characteristics



 $T_{J}\text{-Junction Temperature}({}^{\circ}\!\mathbb{C}\,)$

Figure 4 Drain Current



I_D- Drain Current (A)

Figure 6 Drain-Source On-Resistance



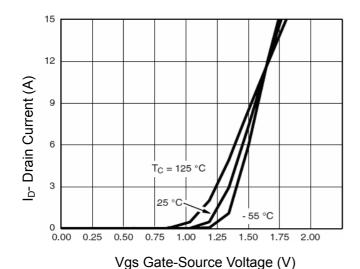
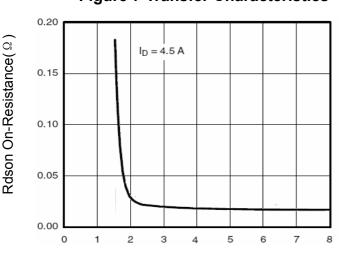


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs. Vgs

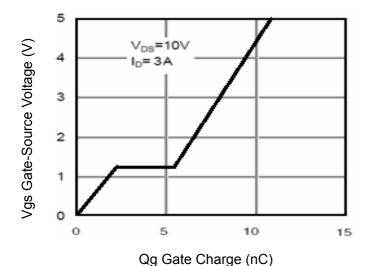


Figure 11 Gate Charge

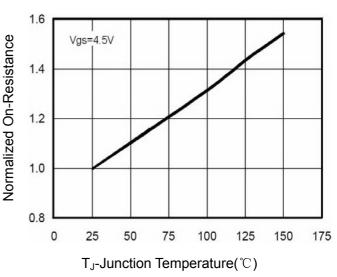
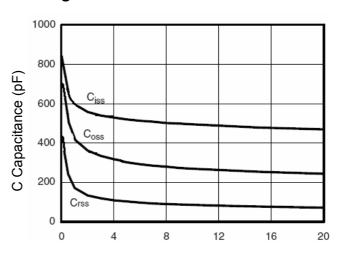
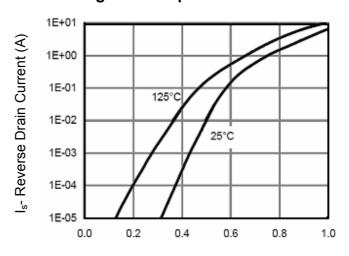


Figure 8 Drain-Source On-Resistance



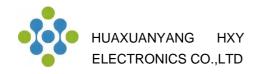
Vds Drain-Source Voltage (V)

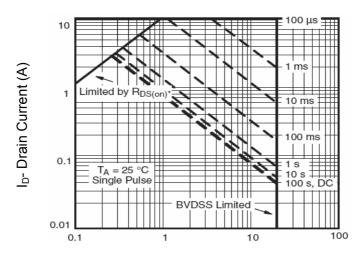
Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area

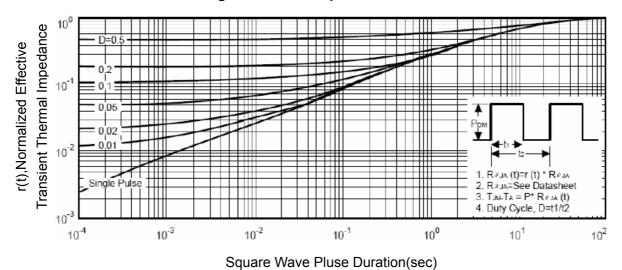
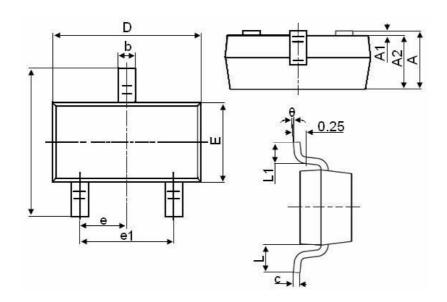


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3LPackage Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L		0.550REF	
L1	0.300	0.600	
θ	0°	8°	

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